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SERIAL NO.

1035-616

Unknown

APPLICANT

SUGIHARA ET AL.

FILING DATE

TC/A.U.

December 16, 2005

~~Unknown~~

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, etc.)

[illegible]

*Examiner

Date Considered

10/29/07

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**INFORMATION DISCLOSURE
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SERIAL NO.

10/560.907

GROUP

~~2131~~ 2815

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

							TRANSLATION	
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
J.K.	2000-150900 A	5-2000	JP			partial		
J.K.	2000-277534 A	10-2000	JP			partial		
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J.K.	Hoffman et al, "ZnO-based transparent thin-film transistors", Applied Physics Letters, vol. 82, no. 5, 3 February 2003, pp.733-735
J.K.	Carcia et al, "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, vol. 82, no. 7, 17 February 2203, pp. 1117-1119
J.K.	Nishii et al, "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., vol. 42, 2003, Part 2, no. 4A 1 April 2003 ©2003 The Japan Society of Applied Physics, pp. L347-L349

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J.K.	Hoffman et al, "ZnO-based transparent thin-film transistors", Applied Physics Letters, vol. 82, no. 5, 3 February 2003, pp.733-735
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*Examiner	<i>Wanda D.</i>	Date Considered	10/29/07
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